

ABSTRACT OF THE INVENTION

The invention includes a non-magnetic physical vapor deposition target. The target has at least 30 atom percent total of one or more of Co, Ni, Ta, Ti, Pt, Mo and W, and at least 10 atom percent silicon. The target also has one phase and not more than 1% of any additional phases other than said one phase. In another aspect, the invention includes a non-magnetic physical vapor deposition target consisting essentially of Co and/or Ni, silicon, and one phase.